

AMENDMENTS TO THE SPECIFICATION

Please replace the title with the following:

METHOD OF FORMING A FLIP CHIP

Please replace Paragraph [0001] with the following paragraph rewritten in amendment format:

CROSS-REFERENCE TO RELATED APPLICATIONS

[0001] This application is a divisional of United States Patent Application No. 10/136,119 filed on ~~May 2, 2002~~May 1, 2004, which is hereby incorporated by reference in its entirety. The content of co-pending U.S. application No. 10/051,965, filed January 16, 2002, is also incorporated by reference in its entirety.

Please replace Paragraph [0005] with the following paragraph rewritten in amendment format:

[0005] A method of forming a flip chip assembly is provided comprising a device
comprises providing a semiconductor die having a core area and a substrate. The
~~semiconductor die has a core area and a periphery area. The periphery area includes~~
an electrostatic discharge (ESD) structure. The semiconductor die includes and
~~includes at least one power conductor, to supply power between the core area and the~~
~~periphery. The periphery includes an ESD structure. A substrate having a source of~~
power is provided. The substrate is coupled to the semiconductor die via a plurality of
~~electrically conductive bumps. A first connection circuit is located within the~~

semiconductor die core area to couple power between the substrate and the semiconductor die power conductor. ~~An electrically conductive bump provides a connection between the first connection circuit and the substrate.~~ The ESD structure is electrically ~~circuit is located outside of the semiconductor die core area and is coupled to the first connection circuit.~~ The first connection circuit is electrically coupled to the substrate via a conductive bump.

Please add the following paragraphs:

[0005.1] In other features, the first connection circuit is a first under ball metallization (UBM). A second UBM is located over the ESD structure. The first UBM is electrically coupled to the second UBM on the substrate.

[0005.2] In other features, a second UBM is located over the ESD structure. The first UBM is electrically coupled to the second UBM on the semiconductor die. The semiconductor die further comprises a redistribution layer. The first UBM is electrically coupled to the second UBM on the redistribution layer.

[0005.3] In still other features, the semiconductor die includes a metallization side and an opposite side. The metallization side is electrically coupled to the substrate. The opposite side of the semiconductor die is thermally coupled to a heat sink. The substrate is electrically coupled to a first surface of a package substrate via a plurality of bond wires. The opposite side of the semiconductor die is adhesively bonded to the heat sink.

Please add the following paragraph:

[0011.1] Figure 6 is a flowchart illustrating steps for forming a flip chip assembly.

Please amend the Abstract section of the specification as rewritten in amendment format.

A method of forming a flip chip device comprises providing assembly comprising a semiconductor die having a core area and a periphery area. The periphery area includes an electrostatic discharge ESD structure. The semiconductor die including includes at least one power conductor, ~~to supply power between the core area and the periphery.~~ A substrate ~~is having a source of power is provided.~~ coupled to the semiconductor die via a plurality of electrically conductive bumps. A first connection circuit is located within the semiconductor die core area to couple power between the substrate and the semiconductor die power conductor. ~~An~~ The ESD structure is electrically coupled to conductive bump provides a connection between the first connection circuit and the substrate. The ESD structure ~~is coupled to the first connection circuit~~ is electrically coupled to the substrate via a conductive bump.